

PNP SILICON LOW POWER TRANSISTOR

Qualified per MIL-PRF-19500/354

Devices

2N2604

2N2605

Qualified Level

JAN, JANTX
JANTXV

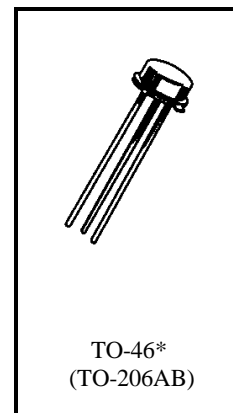
MAXIMUM RATINGS

Ratings	Symbol	2N2604	2N2605	Units
Collector-Base Voltage	V_{CBO}	80	70	Vdc
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current	I_C	30		mAdc
Total Power Dissipation @ $T_A = +25^{\circ}\text{C}^{(1)}$	P_T	400		mW/ $^{\circ}\text{C}$
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.437	$^{\circ}\text{C}/\text{mW}$

1) Derate linearly 2.28 mW/ $^{\circ}\text{C}$ above $T_A = +25^{\circ}\text{C}$



TO-46*
(TO-206AB)

*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Base Breakdown Voltage $I_C = 10 \mu\text{Adc}$	2N2604 2N2605	$V_{(BR)CBO}$	80 70	Vdc
Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$		$V_{(BR)CEO}$	60	Vdc
Emitter-Base Breakdown Current $I_E = 10 \mu\text{Adc}$		$V_{(BR)EBO}$	6.0	Vdc
Collector-Base Cutoff Current $V_{CB} = 50 \text{ Vdc}$		I_{CBO}	10	ηAdc
Emitter-Base Cutoff Current $V_{EB} = 5.0 \text{ Vdc}$		I_{EBO}	2.0	ηAdc
Collector-Emitter Cutoff Current $V_{CE} = 50 \text{ Vdc}$		I_{CES}	10	ηAdc

2N2604, 2N2605 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS (2)				
Forward-Current Transfer Ratio I _C = 10 µAdc, V _{CE} = 5.0 Vdc 2N2604 2N2605 I _C = 500 µAdc, V _{CE} = 5.0 Vdc 2N2604 2N2605 I _C = 10 mAdc, V _{CE} = 5.0 Vdc 2N2604 2N2605	h _{FE}	40 100 60 150 40 100	120 300 180 450 160 400	
Collector-Emitter Saturation Voltage I _C = 10 mAdc, I _B = 500 µAdc	V _{CE(sat)}		0.3	Vdc
Base-Emitter Saturation Voltage I _C = 10 mAdc, I _B = 500 µAdc	V _{BE(sat)}	0.7	0.9	Vdc

DYNAMIC CHARACTERISTICS

Small-Signal Short-Circuit Input Impedance I _C = 1.0 mAdc, V _{CB} = 5.0 Vdc, f = 1.0 kHz 2N2604 2N2605	h _{ie}	1.0 2.0	10 20	kΩ
Small-Signal Open-Circuit Output Admittance I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz 2N2604 2N2605			40 60	µmhos
Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz 2N2604 2N2605	h _{fe}	60 150	180 450	
Magnitude of Small-Signal Forward Current Transfer Ratio I _C = 0.5 mAdc, V _{CE} = 5.0 Vdc, f = 30 MHz	h _{fe}	1.0	8.0	
Output Capacitance V _{CB} = 5.0 Vdc, I _E = 0, 100 kHz ≤ f ≤ 1.0 MHz	C _{obo}		6.0	pF
Noise Figure V _{CE} = 5.0 Vdc, I _C = 10 µAdc, R _g = 10 kΩ, f = 100 Hz V _{CE} = 5.0 Vdc, I _C = 10 µAdc, R _g = 10 kΩ, f = 1.0 kHz V _{CE} = 5.0 Vdc, I _C = 10 µAdc, R _g = 10 kΩ, f = 10 kHz	F ₁ F ₂ F ₃		5.0 3.0 3.0	dB

(2) Pulse Test: Pulse Width = 300µs, Duty Cycle ≤ 2.0%.